

N-Channel Power MOSFET

800V, 0.3A, 21.6Ω

FEATURES

- Advanced planar process
- 100% avalanche tested
- Fast switching

APPLICATION

- Power Supply
- Lighting

KEY PERFORMANCE PARAMETERS			
PARAMETER	R VALUE UNIT		
V _{DS}	800	V	
R _{DS(on)} (max)	21.6	Ω	
Q _g	5	nC	

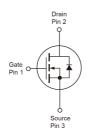






SOT-223





Notes: Moisture sensitivity level: level 3. Per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	800	V
Gate-Source Voltage	V_{GS}	±30	V
Continuous Drain Current	I _D	0.3	А
Pulsed Drain Current (Note 1)	I _{DM}	1	А
Single Pulse Avalanche Energy (Note 2)	E _{AS}	90	mJ
Avalanche Current, Repetitive or Not-Repetitive (Note 1)	I _{AR}	1	А
Total Power Dissipation @ T _C = 25°C	P _{DTOT}	2.1	W
Operating Junction Temperature	TJ	150	°C
Operating Junction and Storage Temperature Range	T _J , T _{STG}	- 55 to +150	°C

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction to Ambient Thermal Resistance	$R_{\Theta JA}$	60	°C/W	

Notes: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. $R_{\Theta JA}$ shown below for single device operation on FR-4 PCB in still air



ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$, $I_D = 1mA$	BV _{DSS}	800			V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 0.15A$	R _{DS(ON)}		18	21.6	Ω
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	3		5	V
Zero Gate Voltage Drain Current	$V_{DS} = 800V, V_{GS} = 0V$	I _{DSS}	1		25	μA
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I _{GSS}	1		±10	μA
Forward Transconductance	$V_{DS} = 40V, I_{D} = 0.1A$	g fs	1	0.36		S
Diode Forward Voltage	$I_S = 0.2A, V_{GS} = 0V$	V_{SD}			1.4	V
Dynamic (Note 3)						
Total Gate Charge		Q_g	1	5	6	
Gate-Source Charge	$V_{DS} = 640V, I_D = 0.3A,$ $V_{GS} = 10V$	Q_gs	1	1		nC
Gate-Drain Charge		Q_gd	1	2		
Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	C _{iss}	-	155	200	
Output Capacitance		C _{oss}		20	26	pF
Reverse Transfer Capacitance		C _{rss}		2.7	4	
Switching (Note 4)						
Turn-On Delay Time	$V_{GS} = 10V, I_D = 0.3A,$ $V_{DS} = 400V, R_G = 25\Omega$	t _{d(on)}	-	10	30	
Turn-On Rise Time		t _r	1	20	50	
Turn-Off Delay Time		t _{d(off)}		16	45	ns
Turn-Off Fall Time		t _f		25	60	

Note:

- 1. Pulse test: pulse width <=300uS, duty cycle <=2%
- 2. $(V_{DD} = 50V, I_{AS}=0.8A, L=170mH, R_{G}=25\Omega)$
- 3. For design reference only, not subject to production testing.
- 4. Switching time is essentially independent of operating temperature.

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ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM1N80CW RPG	SOT-223	2,500pcs / 13" Reel

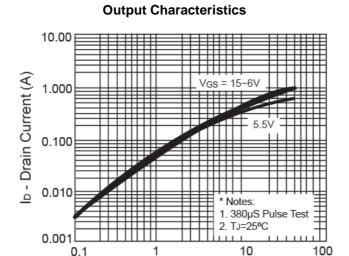
Note:

- 1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- 2. Halogen-free according to IEC 61249-2-21 definition



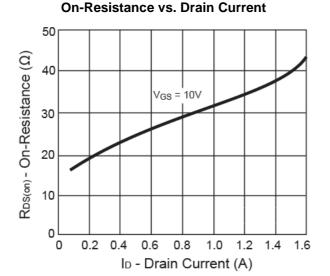
CHARACTERISTICS CURVES

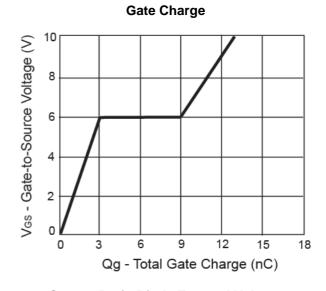
 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

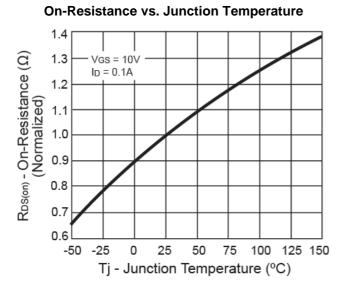


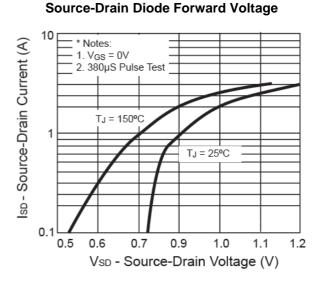
VDS - Drain-to-Source Voltage (V)

Transfer Characteristics 50 40 V_{GS} = 10V V_{GS} = 10V 10 0 0.2 0.4 0.6 0.8 1.0 1.2 1.4 1.6 ID - Drain Current (A)











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CHARACTERISTICS CURVES

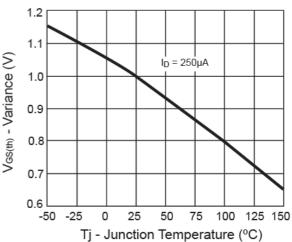
 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

36 30 24

On-Resistance vs. Gate-Source Voltage

R_{DS(on)} - On-Resistance (Ω) $I_D = 0.1A$ 18 12 6 0

Threshold Voltage



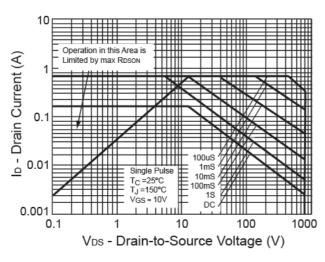
Maximum Safe Operating Area

Vgs - Gate-to-Source Voltage (V)

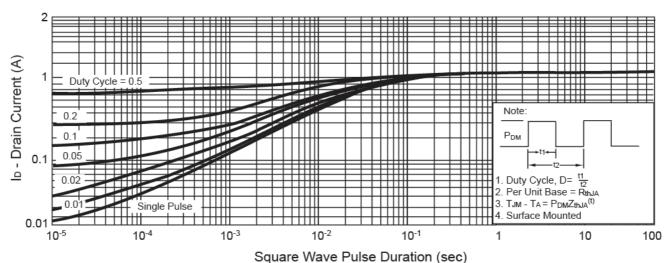
10

12

14



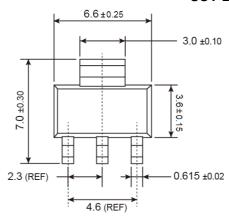
Normalized Thermal Transient Impedance, Junction-to-Ambient

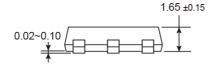


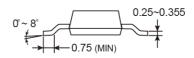


PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

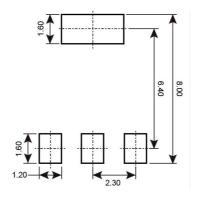
SOT-223







SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr

 $S = May \quad T = Jun \quad U = Jul \quad V = Aug$

W = Sep X = Oct Y = Nov Z = Dec

 $L = \text{Lot Code } (1\sim 9, A\sim Z)$





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